Low Capacitance TVS Array in a SOT23-6 Plastic Package.

Small package saves board space Protects up to four I/O lines & power line Low capacitance for high-speed interfaces Low leakage current and clamping voltage Low operating voltage.

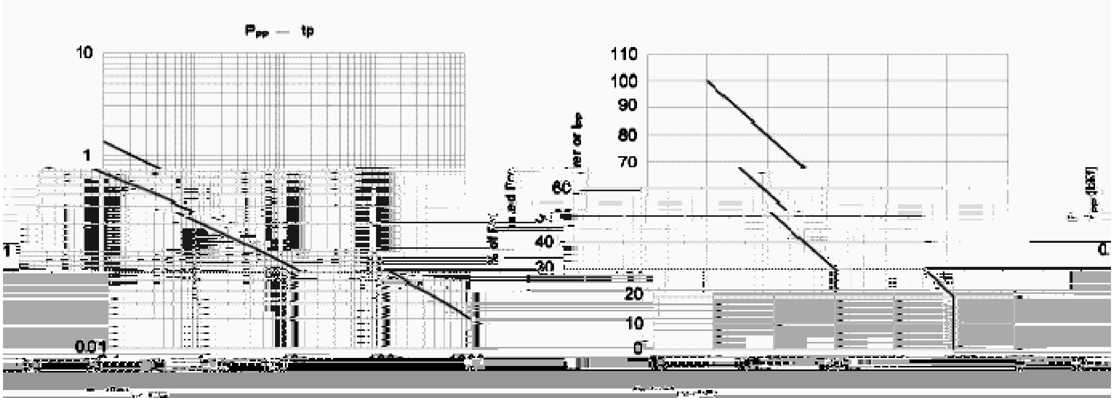
[illegible]

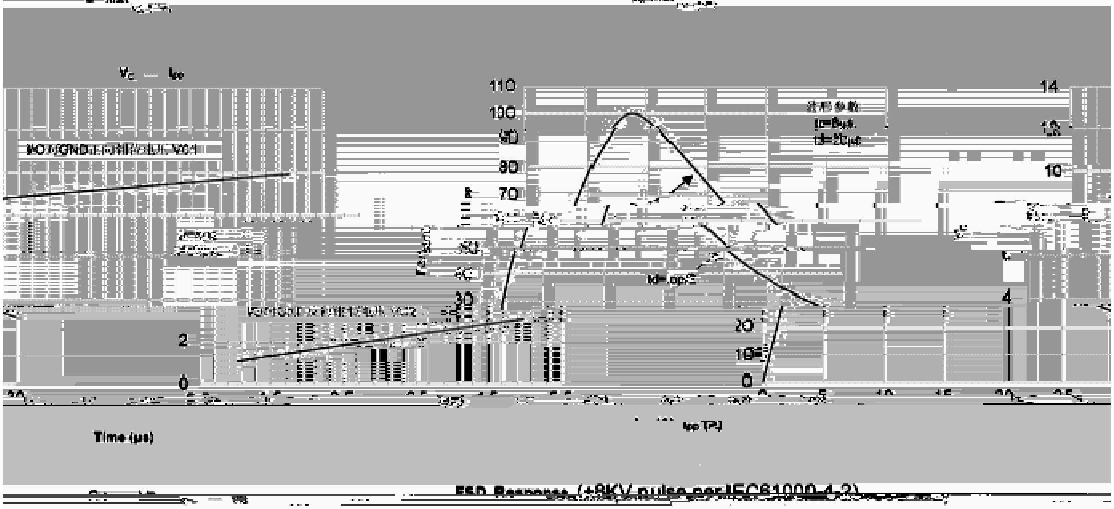
Parameter	Symbol	Rating	Unit
Peak Pulse Power (tp = 8/20μs)	PPP	150	W
Peak Pulse Current (tp = 8/20μs)	IPP	6	A
ESD per IEC 61000-4-2 (Air)	VESD 1 IEC 61000-4-2 (Air)	±15	kV
ESD per IEC 61000-4-2 (Contact)	VESD 2 IEC 61000-4-2 (Contact)	±8	kV
Operating Temperature	TOPR	-55 to 125	
Storage Temperature	TSTG	-55 to 150	

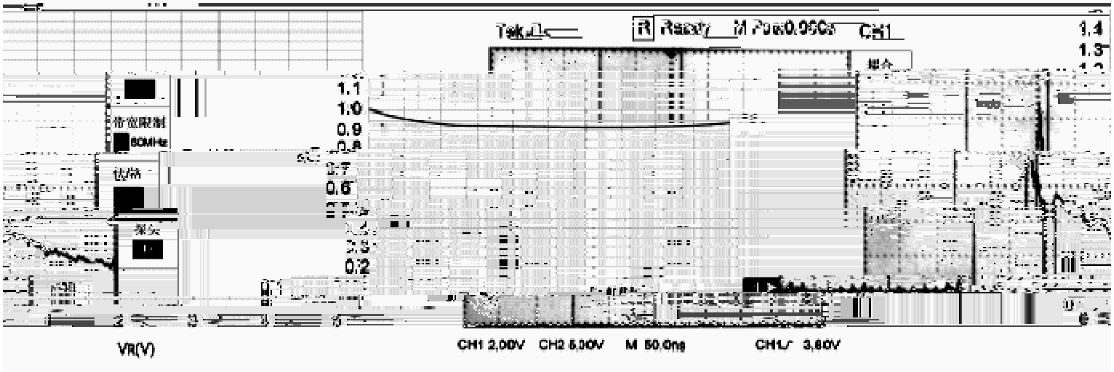
[illegible]

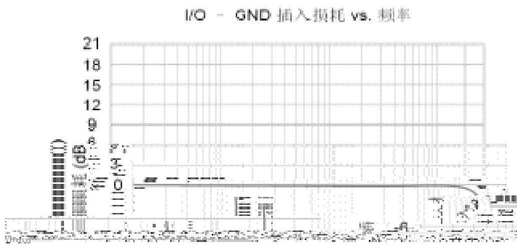
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Reverse Stand-Off Voltage	V_{RWM}	Pin 5 to GND			5	V
Reverse Breakdown Voltage	V_{BR}	Pin 5 to GND It=1mA	6			V
Reverse Leakage Current	I_R	V_{RWM}=5V T=25 Pin 5 to GND			2	μA
Clamping Voltage	V_C	I_{PP}=1A tp=8/20μs Any I/O pin to GND		8.5	12	V
Junction Capacitance	C_{J1}	V_R=0V f=1MHz Any I/O pin to GND			3	pF
Junction Capacitance	C_{J2}	V_R=0V f=1MHz Between I/O pins			1.5	pF

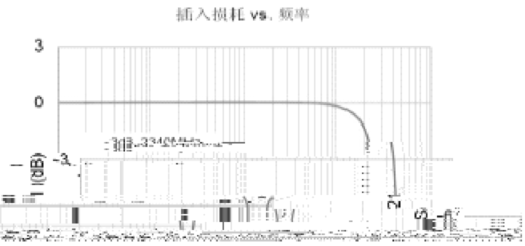
[illegible]


Pₚₚ — tp
10
1
0.01
110
100
90
80
70
60
40
30
20
10
0


Vc — Ipp
I/O对GND正向钳位电压 VC1
I/O对GND反向钳位电压 VC2
2
0
Time (μs)
110
100
90
80
70
30
20
10
0
波形参数
tr=8μs
td=20μs
td=Ipp/2
Ipp (A)
14
12
10
4


ESD Response (+8KV pulse per IEC61000-4-2)
Tek
Ready
M Pos:0.000s
CH1
带宽限制
60MHz
耦合
1.1
1.0
0.9
0.8
0.7
0.6
0.2
VR(V)
CH1 2.00V
CH2 5.00V
M 50.0ns
CH1 ƒ 3.60V
1.4
1.3


I/O - GND 插入损耗 vs. 频率
21
18
15
12
9
6
3
0
插入损耗 (dB)


插入损耗 vs. 频率
3
0
-3
3dB=3340MHz
(dB)

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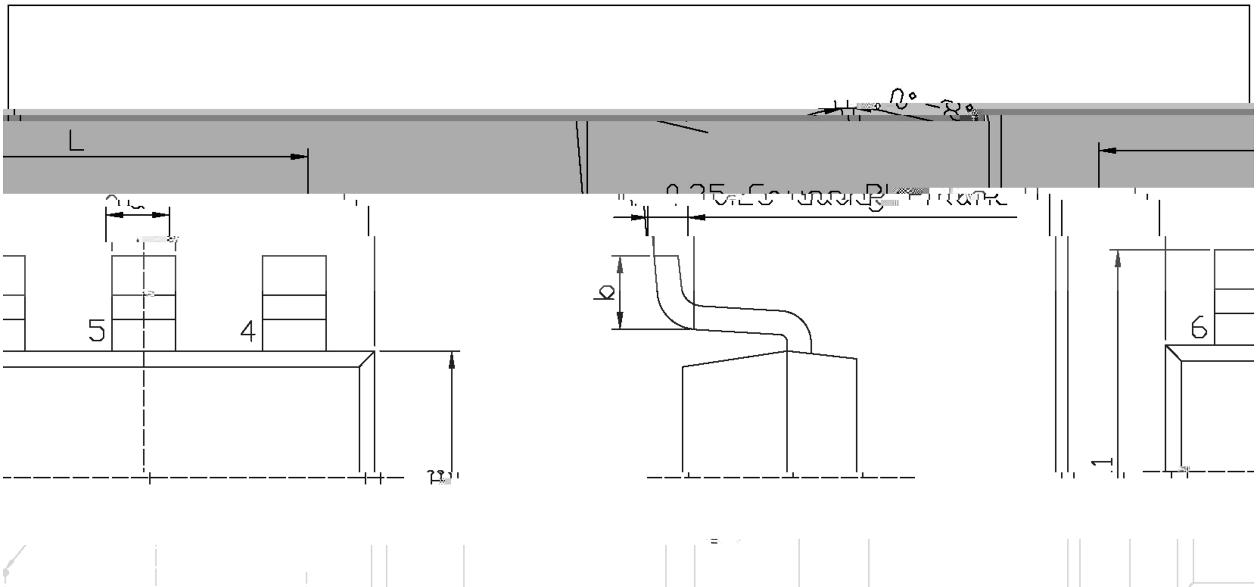

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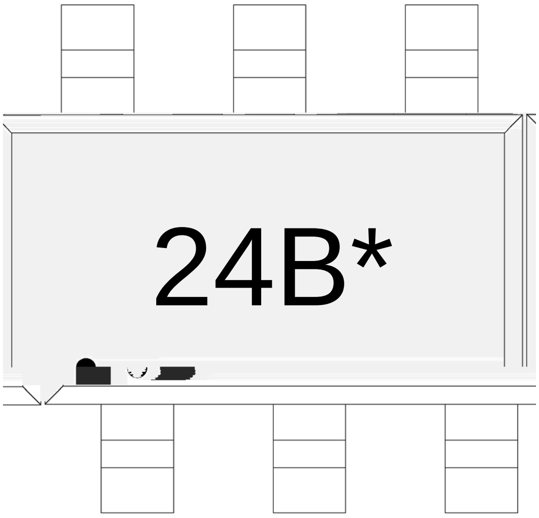

Note:

24B:	Product Type Code
:	Lot No. Code, code change with Lot No.

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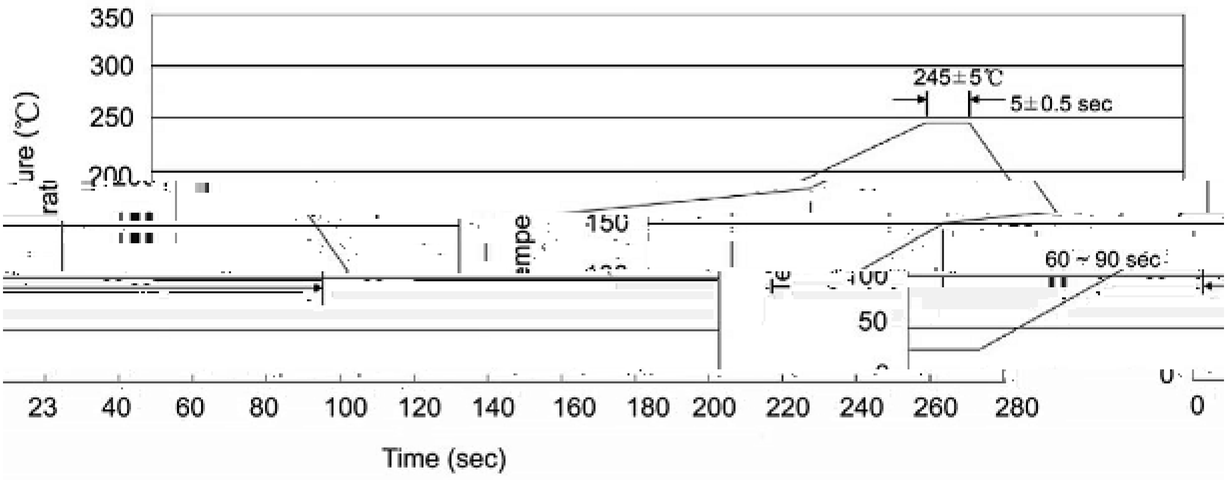

Note:

1 25 150 60 90sec;

1.Preheating:25~150 , Time:60~90sec.

2 245 5 5 0.5sec;

2.Peak Temp.:245 5 , Duration:5 0.5sec.

3 2 10 /sec.

3. Cooling Speed: 2~10 /sec.

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260 5 10 1 sec.

Temp.:260 5 Time:10 1 sec

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/ REEL

Package Type	Units					Dimension		(unit mm^3)

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